

Job Description :

1. Define Flash related memory IP or product design spec, design architecture level and block level circuit. optimize design target (IP macro size, speed, power consumption, etc.) to fit customer's requirements;
2. Verify circuit functionality and performance by simulation;
3. Design memory related blocks including page buffer, high voltage generation, sense amplifier, control logic circuits etc.;
4. Provide design guideline to layout engineer and support layout level optimization.
5. Design memory related DFT circuits and trimming circuits etc.;
6. Responsible for silicon failure analysis and yield improvements in mass production.

Requirement :

1. Solid experiences in transistor level mixed-signal design, familiar with HSPICE, HSIM, ultrasim, or finesim etc. tools.
2. At least 2 years' experience in designing NOR FLASH IP or stand-alone product;
3. Solid knowledge of basic memory design and good understanding of memory device and system;
4. MS of EE with 3+ years or BS of EE with 6+ years;
4. Excellent problem-solving and analytical skills.
5. Good communication skills

职位信息

- 1、负责和参与闪型存储器(Flash Memory)芯片产品规格定义，架构设计，模块设计以及面积、速度、功耗等电路优化工作，
- 2、负责相关电路的仿真验证工作；
- 3、包括架构设计、模拟及高压模块设计、控制逻辑设计等；
- 4、提供版图设计要求并协助版图工程师进行版图的设计优化；
- 5、负责相关的 DFT 和 trimming 电路设计；
- 6、参与项目的流片、制程、验证和调试，负责芯片失效性分析，确认问题根源并提出解决方案。

职位要求：

1. 具有晶体管级混合信号设计的经验，熟悉 HSPICE、HSIM、ULTRASIM、FINESIM 等 EDA 工具；
2. 2 年以上 NOR Flash 设计经验；
3. 深入掌握非易失性存储器设计，并深入理解存储器件和存储系统；
4. 本科或相等学历及以上有 6 年相关设计经验；或者微电子专业硕士毕业 3 年以上电路设计经验；
5. 具有团队工作能力可以和 Foundry 厂进行日常交流。